

LMNDD10N20 200V N-Channel MOSFET

Features

- 200V,8A, $R_{DS(ON)} = 400m\Omega @ V_{GS} = 10V$
- Improved dv/dt capability
- Fast switching
- V_{GS} Guaranteed $\pm 25V$
- Green Device Available
- TO-252-2L package design

These devices are well suited for high efficiency fast switching applications.

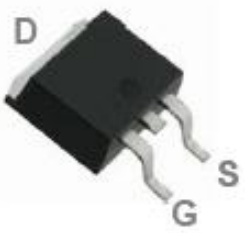
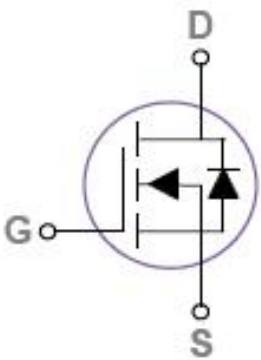
Product Description

These N-Channel enhancement mode power field effect transistors are using trench DMOS technology. This advanced technology has been especially tailored to minimize on-state resistance, provide superior switching performance, and withstand high energy pulse in the avalanche and commutation mode.

Applications

- Networking
- Load Switch
- LED Applications
- Li Battery Pack Applications

Pin Configuration

| LMNDD10N20DF (TO252-2L) | |
|---|---|
|  |  |
| Description | |
| Gate | |
| Source | |
| Drain | |

Ordering Information

| Part Number | P/N | PKG Code | Pb Free Code | Package | Quantity Reel |
|--------------|------------|----------|--------------|-----------|---------------|
| LMNDD10N20DF | LMNDD10N20 | D | F | TO-252-2L | 2500 pcs |

Marking Information

| Part Marking | Part Number | LFC code |
|-------------------|-------------|----------|
| DD10N20 XWMMMM | DD10N20 | XWMMMM |

Absolute Maximum Ratings

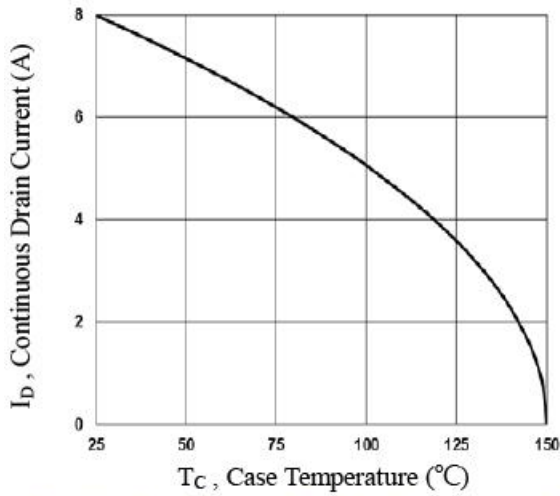
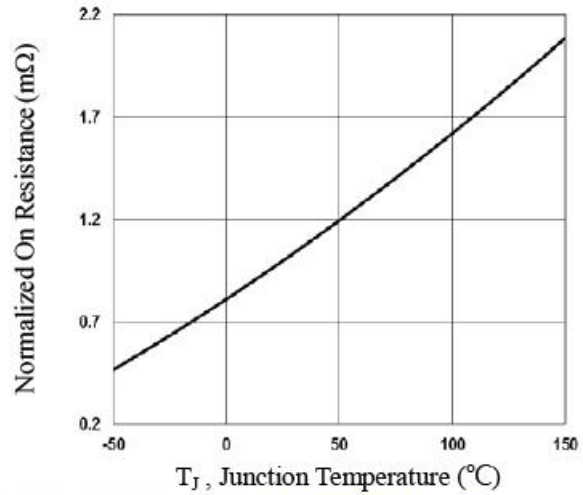
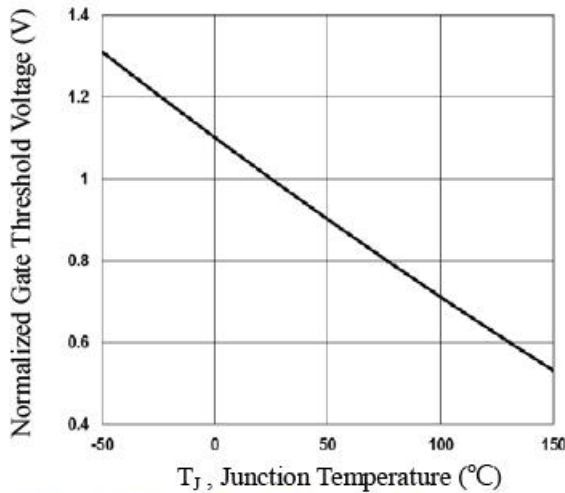
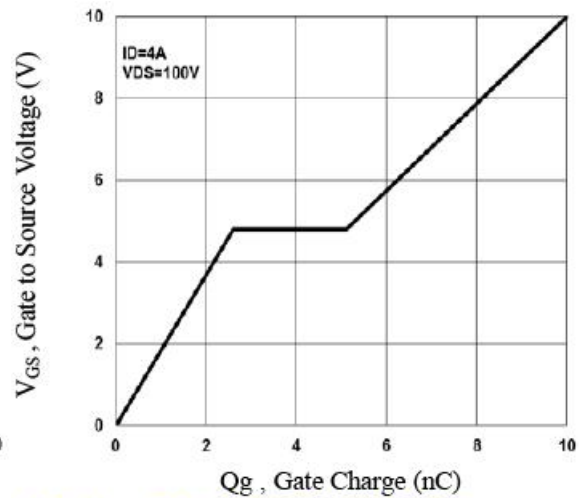
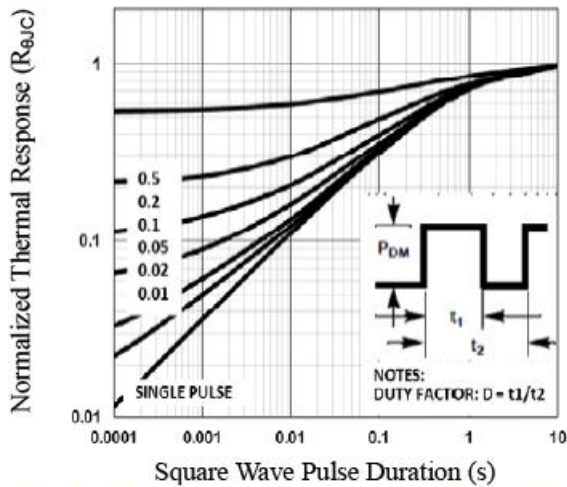
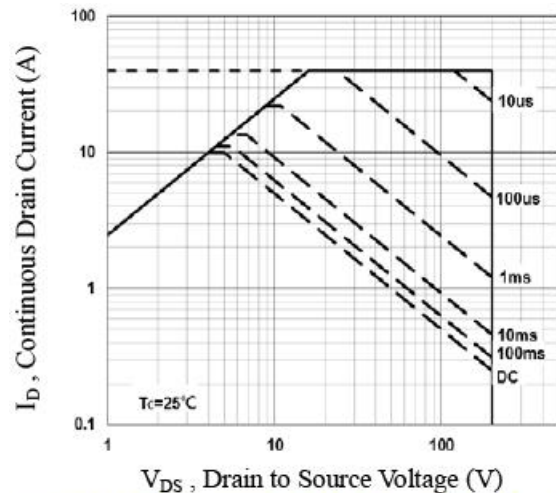
 (T_A=25°C Unless otherwise noted)

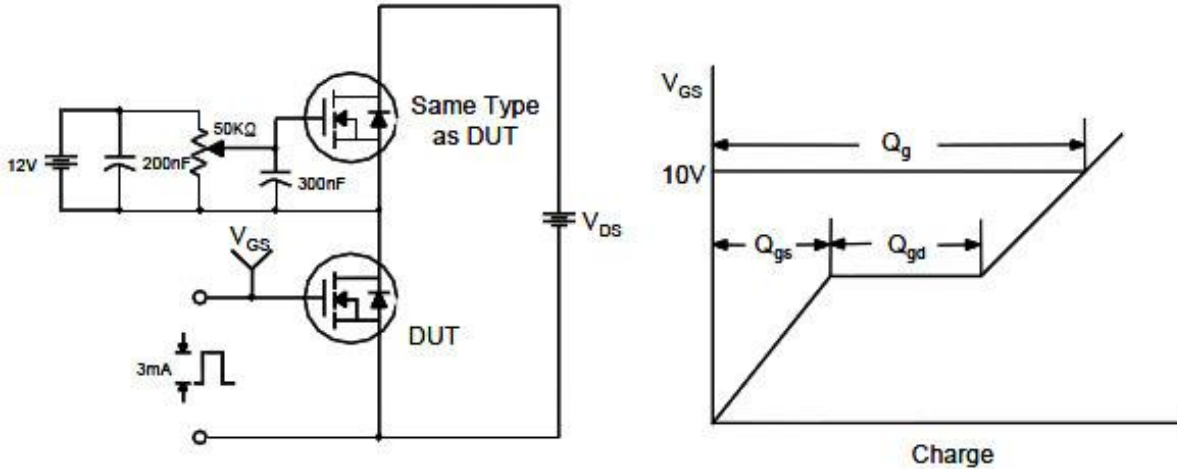
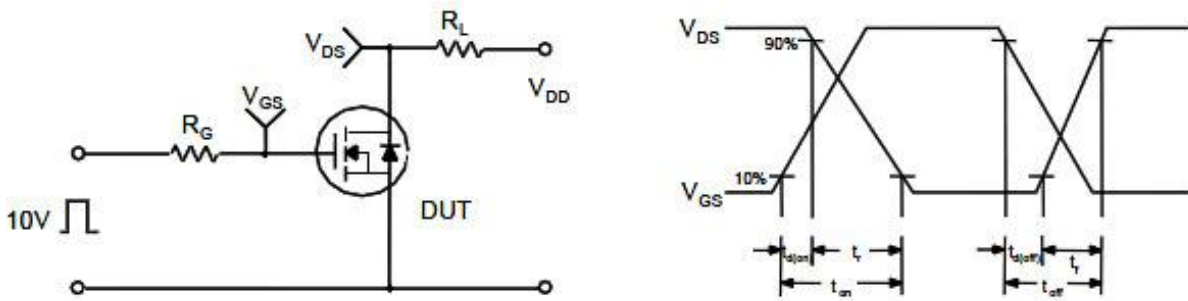
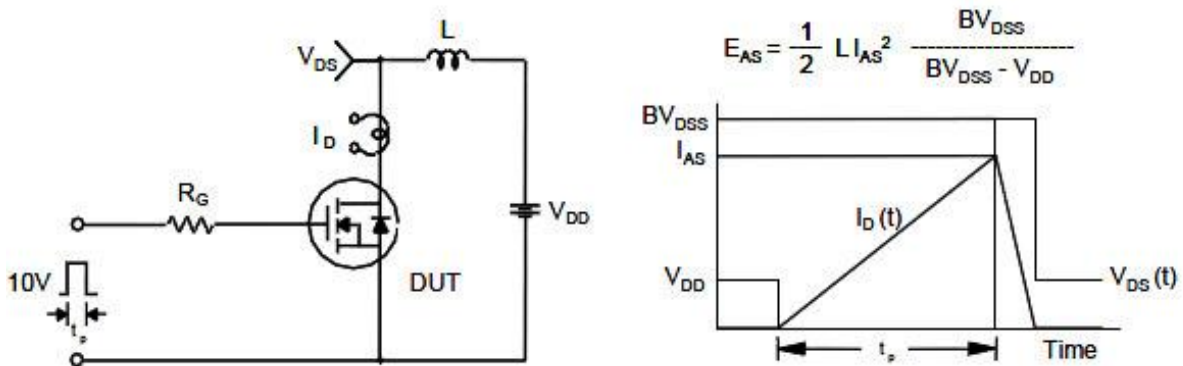
| Symbol | Parameter | Typical | Unit |
|------------------|---|-----------------------|------|
| V _{DS} | Drain-Source Voltage | 200 | V |
| V _{GS} | Gate-Source Voltage | ±25 | V |
| I _D | Continuous Drain Current | T _A =25°C | 8 |
| | | T _A =100°C | 5 |
| I _{DM} | Pulsed Drain Current | 32 | A |
| P _D | Power Dissipation(T _C =25°C) | 50 | W |
| | Power Dissipation(Derate above 25°C) | 0.4 | W/°C |
| T _J | Operating Junction Temperature Range | -55 to +150 | °C |
| T _{STG} | Storage Temperature Range | -55 to +150 | °C |
| R _{θJA} | Thermal Resistance-Junction to Ambient | 62 | °C/W |
| R _{θJC} | Thermal Resistance-Junction to Case | 2.5 | °C/W |

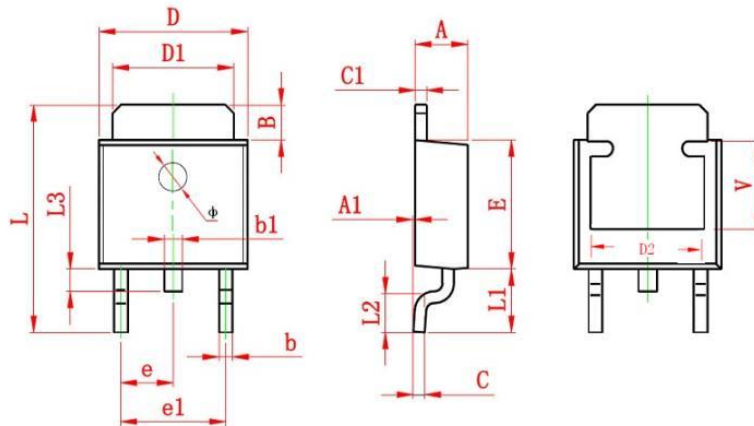
Electrical Characteristics

 (T_A=25°C Unless otherwise noted)

| Symbol | Parameter | Conditions | Min | Typ | Max | Unit |
|----------------------|---------------------------------|---|-----|-----|------|------|
| Static | | | | | | |
| V _{(BR)DSS} | Drain-Source Breakdown Voltage | V _{GS} =0V, I _D =250uA | 200 | | | V |
| V _{GS(th)} | Gate Threshold Voltage | V _{DS} =V _{GS} , I _D =250uA | 2 | 3 | 4 | V |
| I _{GSS} | Gate Leakage Current | V _{DS} =0V, V _{GS} =±25V | | | ±100 | nA |
| I _{DSS} | Zero Gate Voltage Drain Current | V _{DS} =160V, V _{GS} =0V | | | 1 | uA |
| | | V _{DS} =160V, V _{GS} =0V, T _J =125°C | | | 30 | |
| I _S | Continuous Source Current | V _G =V _D =0, Force Current | | | 8 | A |
| I _{SM} | Pulsed Source Current | | | | 32 | |
| R _{DS(on)} | Drain-Source On-Resistance | V _{GS} =10V, I _D =4A | | 320 | 400 | mΩ |
| V _{SD} | Diode Forward Voltage | V _{GS} =0V, I _S =1A | | | 1.3 | V |
| t _{rr} | Reverse Recovery Time | V _{GS} =0V, I _S =1A, di/dt=100A/us | | 67 | | ns |
| Q _{rr} | Reverse Recovery Charge | | | | 114 | |
| Dynamic | | | | | | |
| C _{iss} | Input Capacitance | V _{DS} =30V, V _{GS} =0V, f=1MHz | | 500 | 730 | pF |
| C _{oss} | Output Capacitance | | | 41 | 60 | |
| C _{rss} | Reverse Transfer Capacitance | | | 16 | 30 | |
| R _g | Gate Resistance | V _{DS} =0V, V _{GS} =0V, f=1MHz | | 3 | 6 | Ω |
| Q _g | Total Gate Charge | V _{DS} =100V, V _{GS} =10V, I _D =4A | | 10 | 15 | nC |
| Q _{gs} | Gate-Source Charge | | | 2.6 | 4 | |
| Q _{gd} | Gate-Drain Charge | | | 2.5 | 5 | |
| t _{d(on)} | Turn-On Time | V _{DD} =30V, I _D =1A, V _{GS} =10V, R _G =6Ω | | 9 | 16 | ns |
| T _r | | | | 8 | 15 | |
| t _{d(off)} | Turn-Off Time | | | 18 | 33 | |
| T _f | | | | 3 | 6 | |

Typical Performance Characteristics

Fig.1 Continuous Drain Current vs. T_c

Fig.2 Normalized $R_{DS(on)}$ vs. T_j

Fig.3 Normalized V_{th} vs. T_j

Fig.4 Gate Charge Waveform

Fig.5 Normalized Transient Impedance

Fig.6 Maximum Safe Operation Area

Typical Performance Characteristics (continue.)
Gate Charge Test Circuit & Waveform

Resistive Switching Test Circuit & Waveforms

Unclamped Inductive Switching Test Circuit & Waveforms


Package Dimension
TO-252-2L


| Dimensions | | | | |
|------------|-------------|--------|-----------|-------|
| Symbol | Millimeters | | Inches | |
| | Min | Max | Min | Max |
| A | 2.200 | 2.400 | 0.087 | 0.094 |
| A1 | 0.000 | 0.130 | 0.000 | 0.005 |
| B | 0.890 | 1.270 | 0.035 | 0.050 |
| b | 0.640 | 0.880 | 0.025 | 0.035 |
| b1 | 0.640 | 0.880 | 0.025 | 0.035 |
| C | 0.430 | 0.580 | 0.017 | 0.023 |
| C1 | 0.430 | 0.600 | 0.017 | 0.024 |
| D | 6.350 | 6.730 | 0.250 | 0.265 |
| D1 | 5.200 | 5.520 | 0.205 | 0.217 |
| E | 5.200 | 6.220 | 0.205 | 0.244 |
| e | 2.300 TYP | | 0.091 TYP | |
| e1 | 4.500 | 4.700 | 0.177 | 0.185 |
| L | 9.400 | 10.400 | 0.370 | 0.409 |
| L1 | 3.100 REF | | 0.122 REF | |
| L2 | 1.400 | 1.780 | 0.055 | 0.070 |
| L3 | 0.600 | 1.000 | 0.024 | 0.039 |
| L4 | 0.600 | 1.100 | 0.024 | 0.043 |
| V | 5.350 REF | | 0.211 REF | |
| D2 | 4.830 REF | | 0.190 REF | |